



BZF05E,2CZ222,2CBG05I

GLASS PASSIVATED SILICON ULTRAHIGH VOLTAGE,

ULTRAFAST RECOVERY DIODE

Features:

1. Silicon diffusion mesa.
2. Glass Passivated package.
3. Small volume, light weight.
4. Small high-temperature leakage.
5. Good thermal stability.
6. High reliability.
7. Implementation of standards: GJB33A-97, QZJ840611



TECHNICAL DATA:

($T_a = 25^\circ\text{C}$)

Parameter name	Symbols	Unit	Specifications			Test Condition
			BZF05E	2CZ222	2CBG05I	
Use for	Ultra-high-frequency, high-voltage boost, rectifier circuit.					
Store temperature	T	$^\circ\text{C}$	-55~+150			
Quality Class			JP, JT, GS, G			
Peak Repetitive Reverse Voltage	V_{RRM}	KV	5	5	10	
Average Forward Current	$I_{F(AV)}$	A	0.5	0.25	0.5	
Average Forward Voltage	V_F	V	9	12	24	$I=I_{F(AV)}$
Non-repeat Forward Surge Current	I_{FSM}	A	10	2	5	Single-phase industrial frequency sine half wave 10ms
Peak Reverse Current	I_{RM1}	μA	5			$V_R=V_{RRM}, T_a=25^\circ\text{C}$
Peak Reverse Current	I_{RM2}	μA	50			$V_R=V_{RRM}, T_a=125^\circ\text{C}$
Junction Temperature	T_{jm}	$^\circ\text{C}$	125	125	150	
Reverse Recovery Time	t_{rr}	μS	0.08	0.3	0.08	$V_R=10\text{V}, I_F=50\text{mA}, R_L=75\text{ohms}$

Outline and Dimensions: